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## 國立臺灣大學 114 學年度碩士班招生考試試題

科目: 電子學(B)

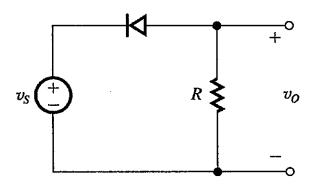
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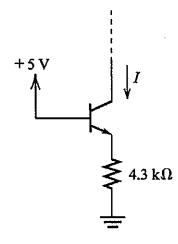
1. (7%) What is harmonic distortion? What causes it?

2. (8%) What is the CMRR? For what types of application is it important?

- 3. (15%) Consider the half-wave rectifier circuit shown on the right. Let  $v_S$  be a sinusoid with 10-V peak amplitude, and let  $R=1~\mathrm{k}\Omega$ . Use the constant-voltage-drop diode model with  $V_D=0.7~\mathrm{V}$ .
  - (a) Sketch the transfer characteristic.
  - (b) Sketch the waveform of  $v_0$ .
  - (c) Find the average value of  $v_0$ .
  - (d) Find the peak current in the diode.
  - (e) Find the PIV of the diode.



- 4. (15%) Suppose we have an NMOS transistor that has  $g_m = 2$  mS and  $r_d = 5$  k $\Omega$  for a Q point of  $V_{GSQ} = 2$  V,  $I_{DQ} = 4$  mA, and  $V_{DSQ} = 10$  V. Sketch the drain characteristics to scale for a small region around the Q point, say, for  $v_{GS} = 1.8$ ,  $v_{GS} = 2.0$ ,  $v_{GS} = 2.2$  V and for  $9.0 < v_{DS} < 11.0$  V.
- 5. (15%) For the constant-current source circuit shown on the right, find the collector current I and the output resistance. The BJT is specified to have  $\beta = 100$ ,  $V_{BE} = 0.7$  V, and  $V_A = 100$  V. If the collector voltage undergoes a change of 10 V while the BJT remains in the active mode, what is the corresponding change in collector current?



- 6. (20%) An op amp with bandwidth  $f_t = 20$  MHz, slew rate SR = 10 V/ $\mu$ s, and output saturation  $V_{omax} = 10$  V is used in the design of a noninverting amplifier. The nominal gain of the noninverting amplifier is 10. Assume a sine-wave input with peak amplitude  $V_i$ .
  - (a) If  $V_i = 0.5$  V, what is the maximum frequency before the output distorts?
  - (b) If f = 200 kHz, what is the maximum value of  $V_i$  before the output distorts?
  - (c) If  $V_i = 50$  mV, what is the useful frequency range of operation?
  - (d) If f = 50 kHz, what is the useful input voltage range?
- 7. (20%) There is a three-input CMOS NAND gate.
  - (a) Draw the circuit diagram of the NAND gate.
  - (b) Draw its equivalent circuit (open and closed switches) if all inputs are high.
  - (c) Redraw (b) if all inputs are low.

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